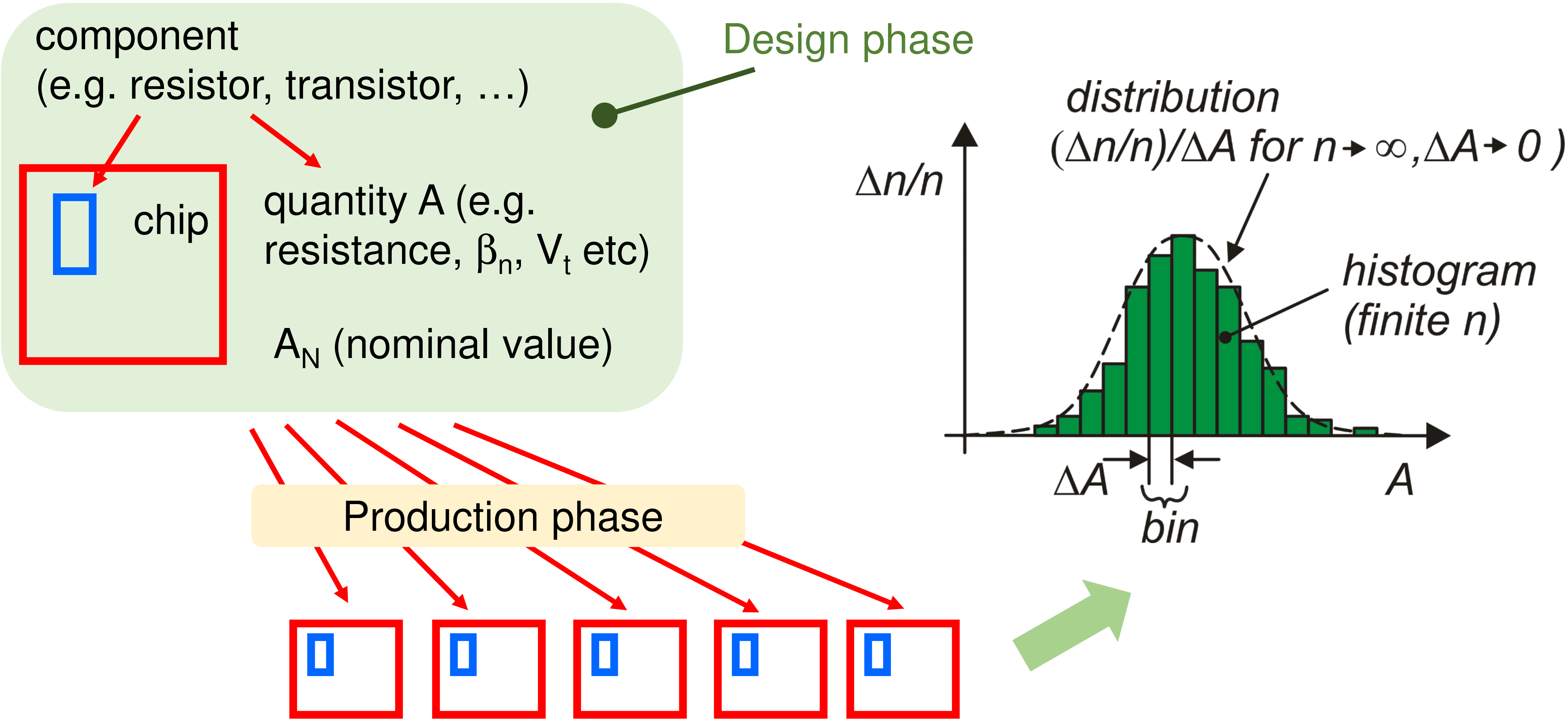
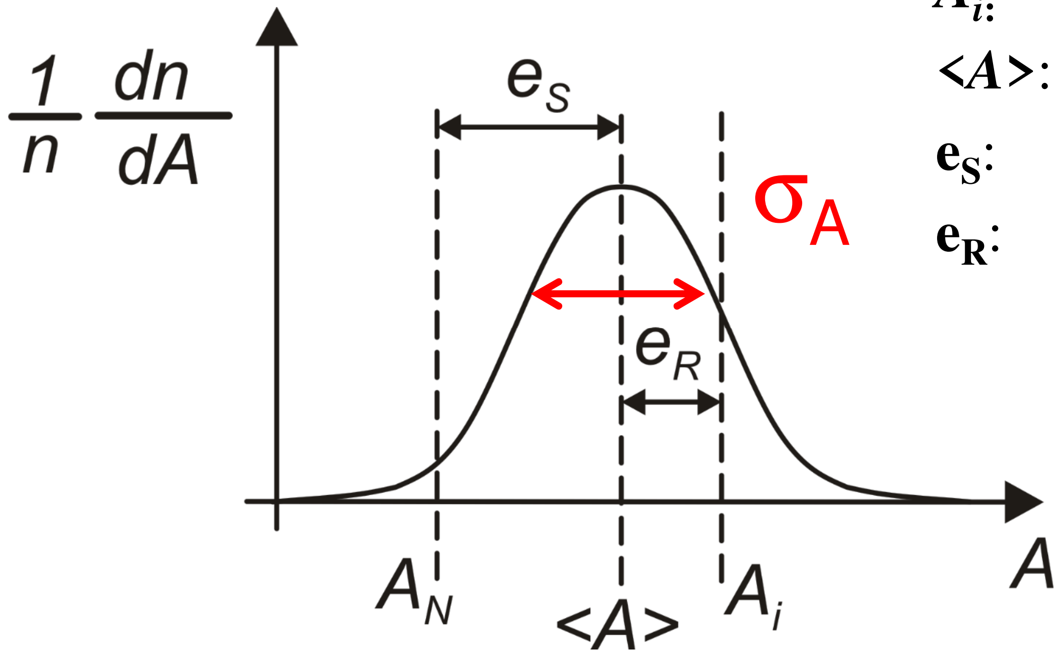
Process Errors in Integrated Circuits



Components of the error and statistical representation



A_N: nominal value

A_i: A for a generic i-th component.

$<A>$: the mean of the distribution.

e_S: Systematic error = $<A>-A_N$

e_R: Random error for the i-th component $e_R = A_i - <A>$.

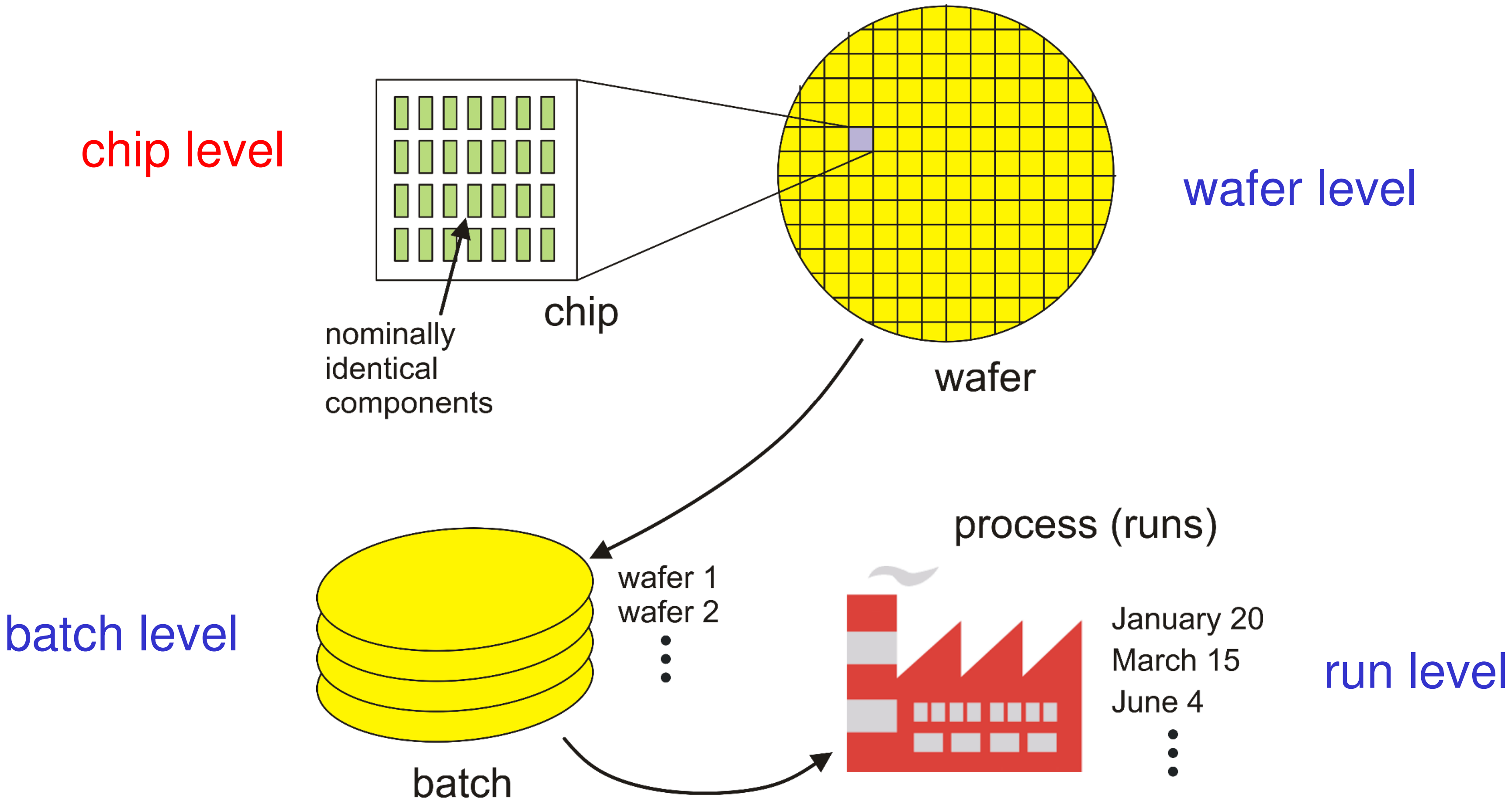
Random error: standard deviation

$$\sigma_A = \sqrt{\left\langle \left(A - <A> \right)^2 \right\rangle}$$

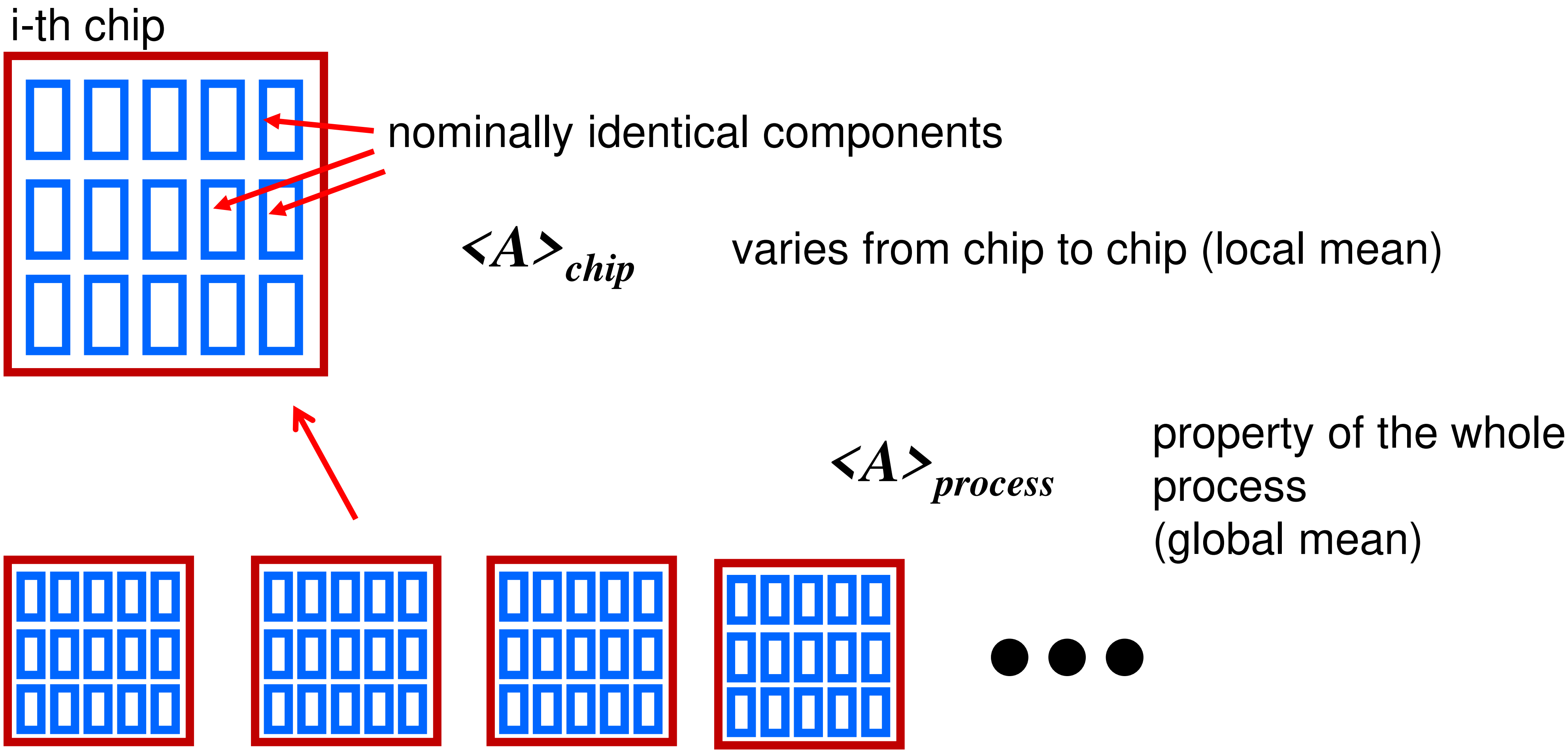
Confidence intervals

Max deviation from the mean	$\pm\sigma$	$\pm 2\sigma$	$\pm 3\sigma$	$\pm 4\sigma$
Fraction of data within the interval	68.3 %	95.4 %	99.7 %	99.994 %
Fraction of data outside the interval	31.7 %	4.6 %	0.3 %	0.006 %

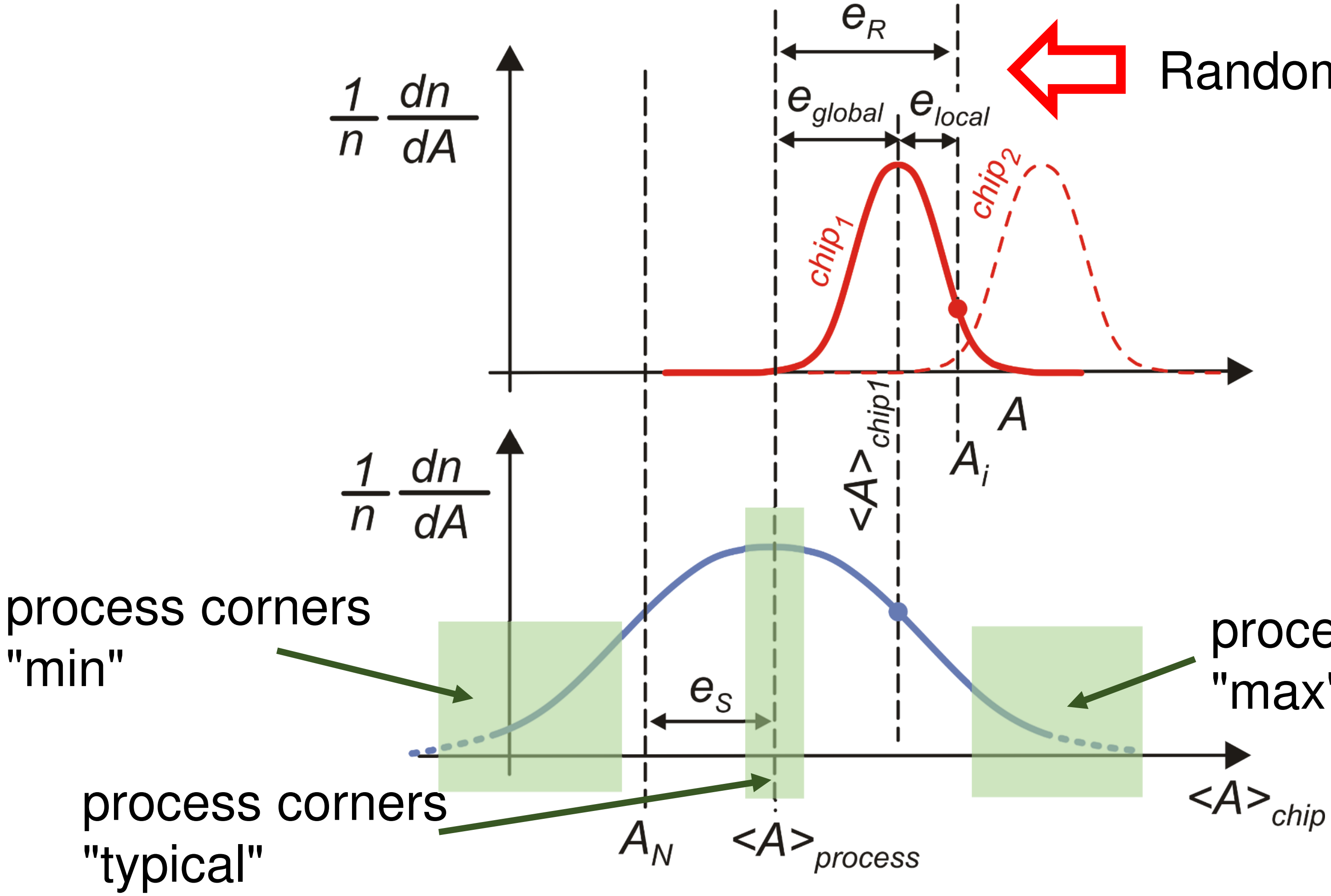
Errors in Integrated Circuits: Levels



Local and global errors: means



Local and global errors

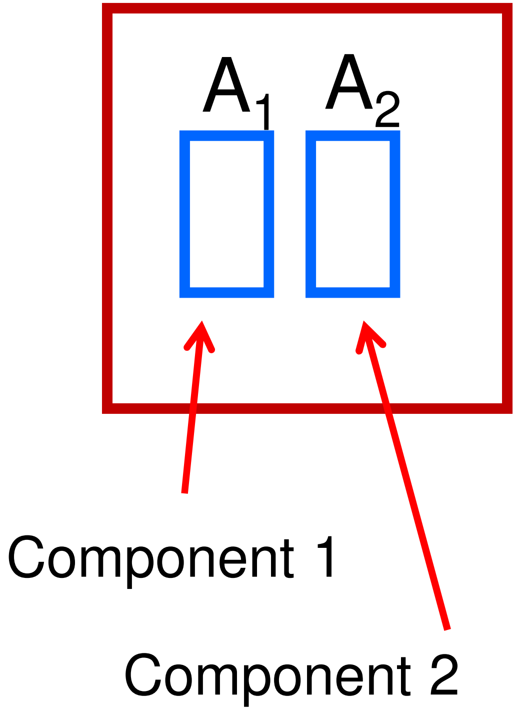


Random errors local and global

In practice, the distribution of local errors is much narrower than shown here

$$\sigma_{global} >> \sigma_{local}$$

Matching errors: definition



Nominally identical

Matching error (or mismatch)

$$\begin{cases} \Delta A = A_1 - A_2 \\ \bar{A} = \dfrac{A_1 + A_2}{2} \end{cases} \Leftrightarrow \begin{cases} A_1 = \bar{A} + \dfrac{\Delta A}{2} \\ A_2 = \bar{A} - \dfrac{\Delta A}{2} \end{cases}$$

Random Matching errors: Main causes

- Microscopic irregularities (local granularity)
- Parameter gradients

Matching errors: Microscopic irregularities

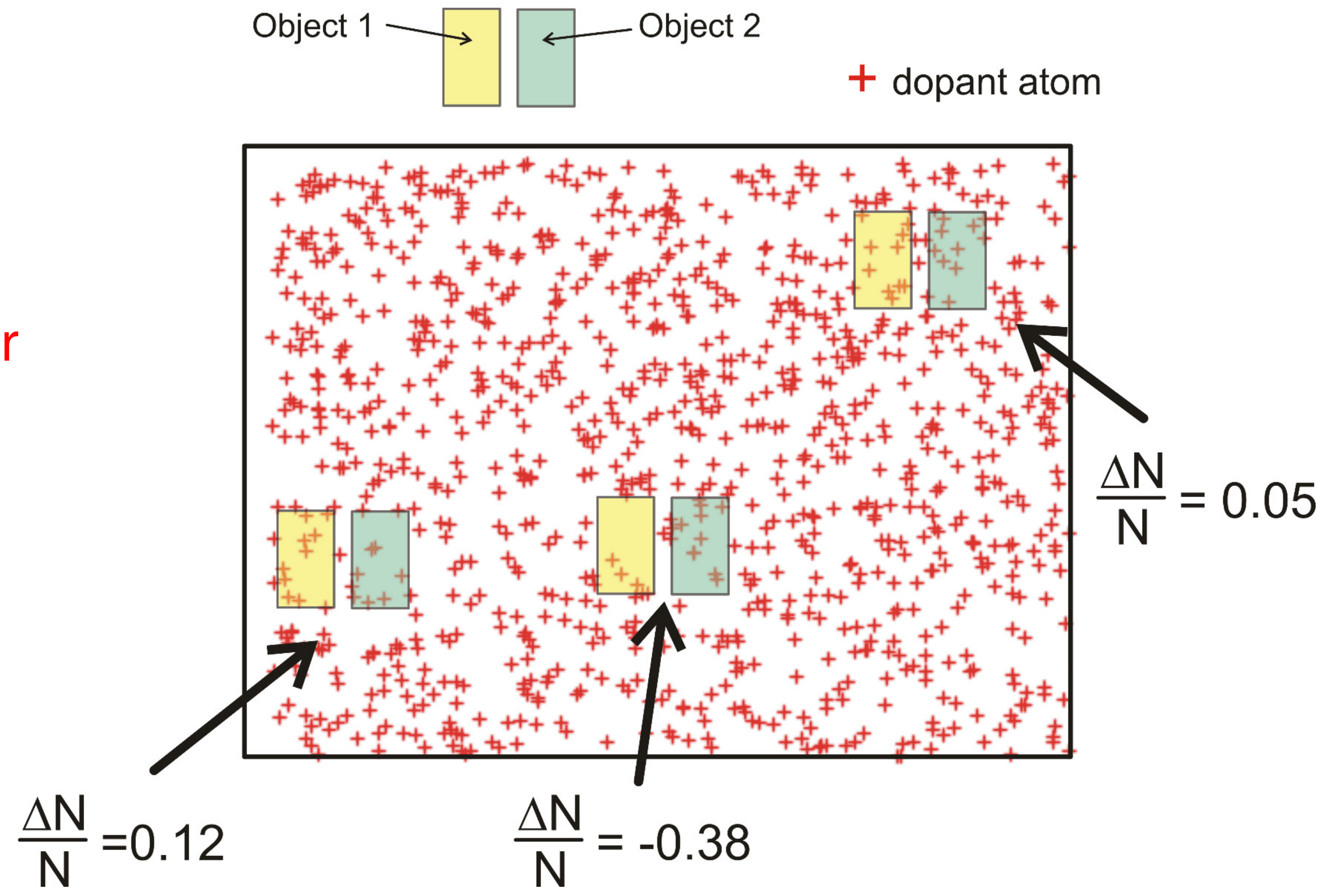
N= number of dopants atoms within the component area

$\Delta N = N_1 - N_2$ matching error

Depending on the position ΔN is subjected to large variations.

Relative matching error:

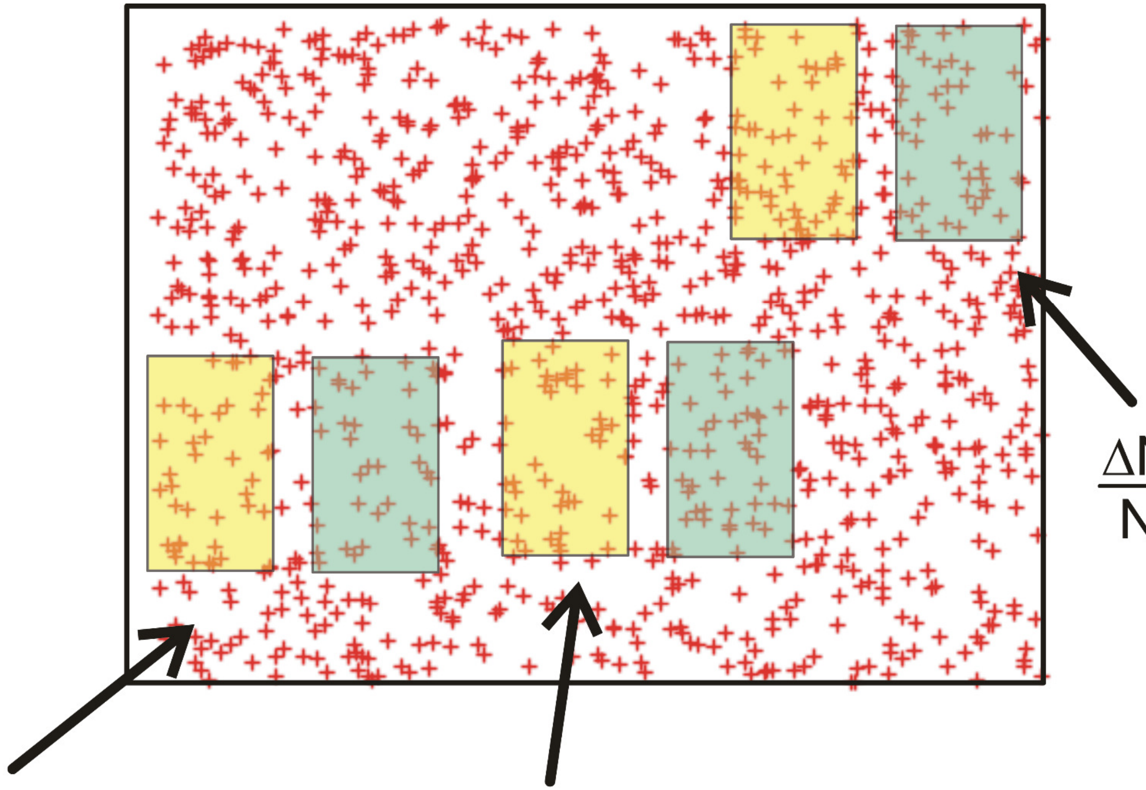
$$\frac{\Delta N}{N} \leftarrow \frac{N_1 + N_2}{2}$$



Matching errors: Microscopic irregularities

- The number of dopants atoms affects several properties such as effective sheet resistance and MOSFET threshold voltage
- The example can be replicated for other quantities, such as oxide thickness, where the crosses in the figure may represent local maxima or minima
- The large fluctuation of $\Delta N/N$ can be ascribed to the small area of the devices shown in the example. For even smaller devices its is likely that one of the two devices does not include any dopant atom : $\Delta N/N$ may exceed unity (100 % error).

Microscopic irregularities: effect of device area



Larger device areas result in smaller **relative** matching errors

$$\frac{\Delta N}{N} = 0.01$$

$$\frac{\Delta N}{N} = 0.04$$

$$\frac{\Delta N}{N} = -0.05$$

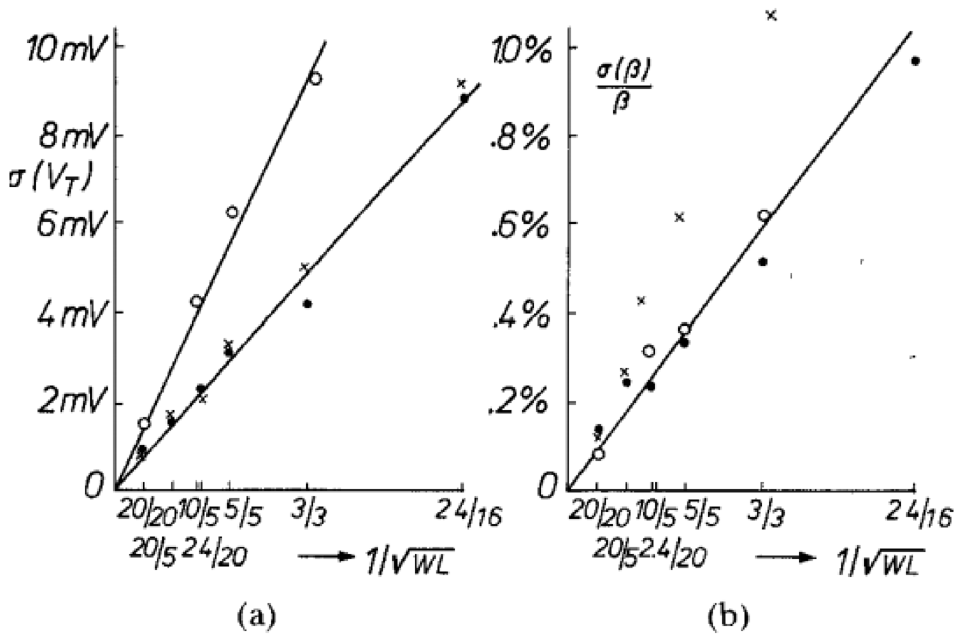
Microscopic irregularities: the Pelgrom model

$$\begin{cases} \sigma_{\Delta V_t} = \dfrac{C_{Vt}}{\sqrt{WL}} \\ \sigma_{\frac{\Delta\beta}{\beta}} = \dfrac{C_{\beta}}{\sqrt{WL}} \end{cases}$$

Mosfet

$$\sigma_{\frac{\Delta R}{R}} = \frac{C_R}{\sqrt{WL}}$$

Resistor



From: Pelgrom et a IEEE J. of Solid State Circuits, 1989l

C_{vt}, C_{β} and C_R are constant parameters of the process Their values are given in the Design Rule Manual, with names that depend on the foundry (there is no general convention).
C_{vt} units are generally V·μm, while C_{β} and C_R ones are μm.

Matching Errors: Gradients

- Gradients indicate that important quantities that affect the device properties are not uniformly distributed on a macroscopic scale. This means that these quantities gradually varies across the chip area.

- Quantities of interest can be, for example:

  -) Dopant density

  -) Oxide thickness

- -) Geometrical process biases (e.g. etching undercut)

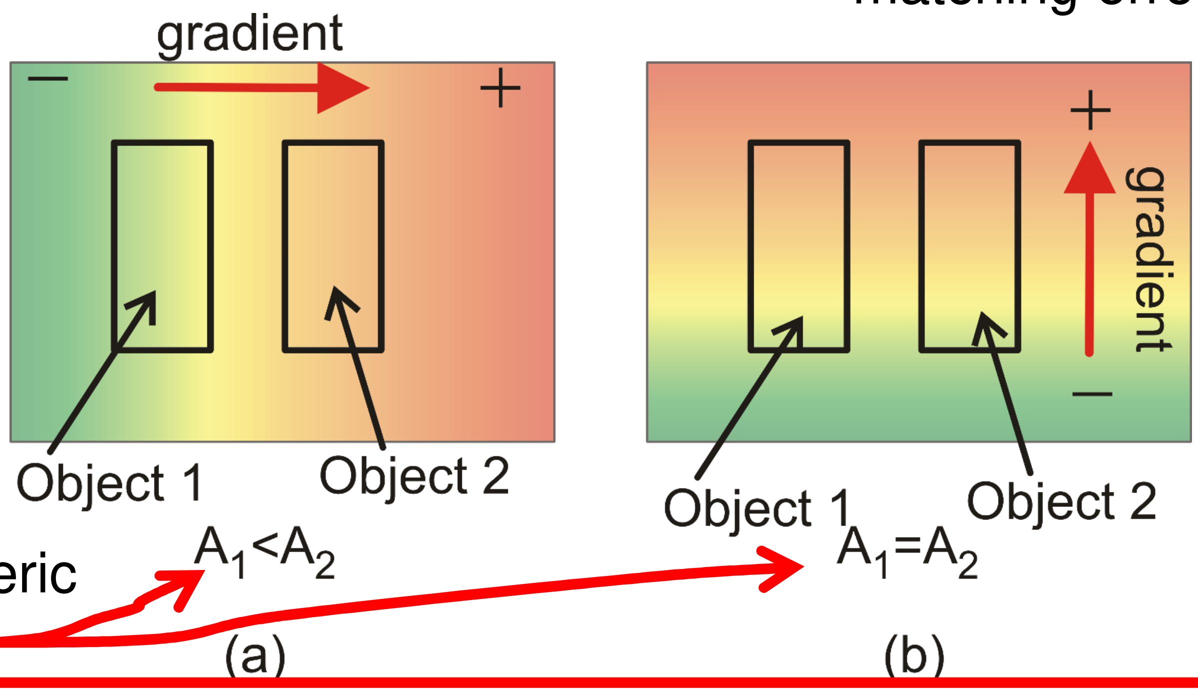
  -) Temperature (e.g. due to power devices present on the chip)

- -) Mechanical stress (mainly due to the packaging process)

Effect of gradients on device matching

Gradient causes matching error

Gradient does not causes matching error

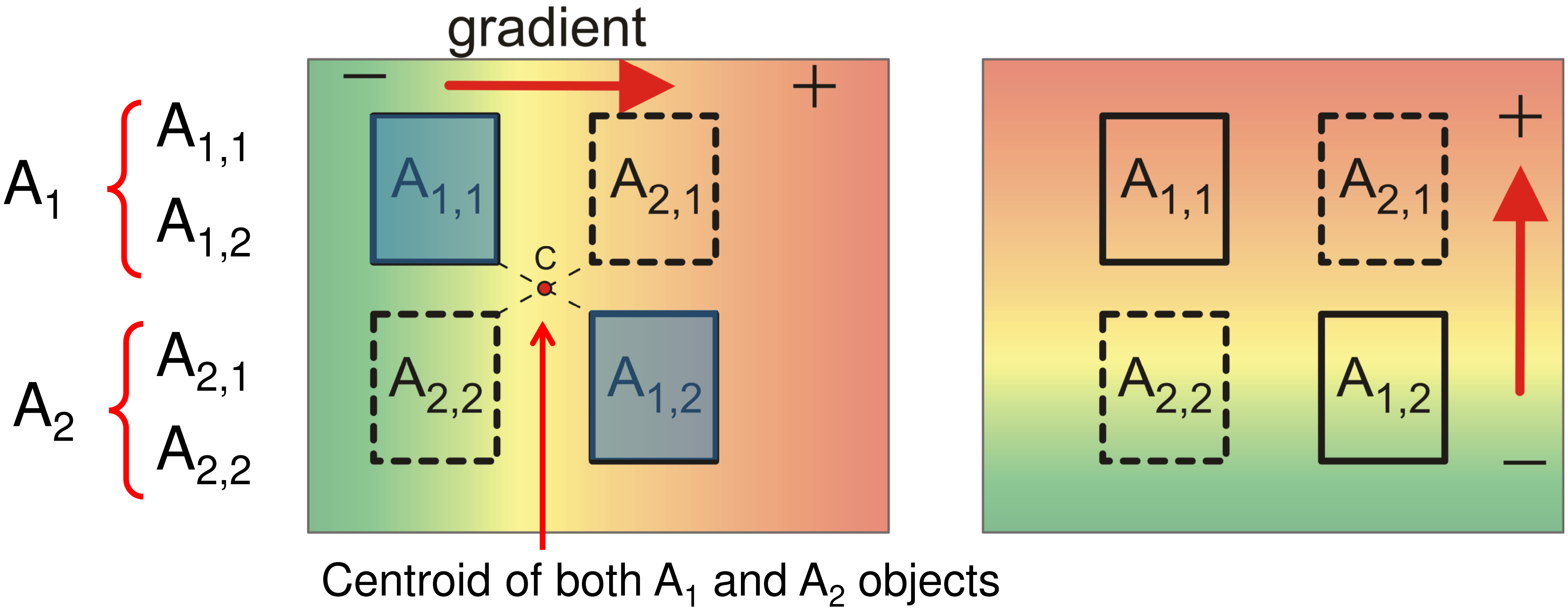


We consider a generic quantity "A"

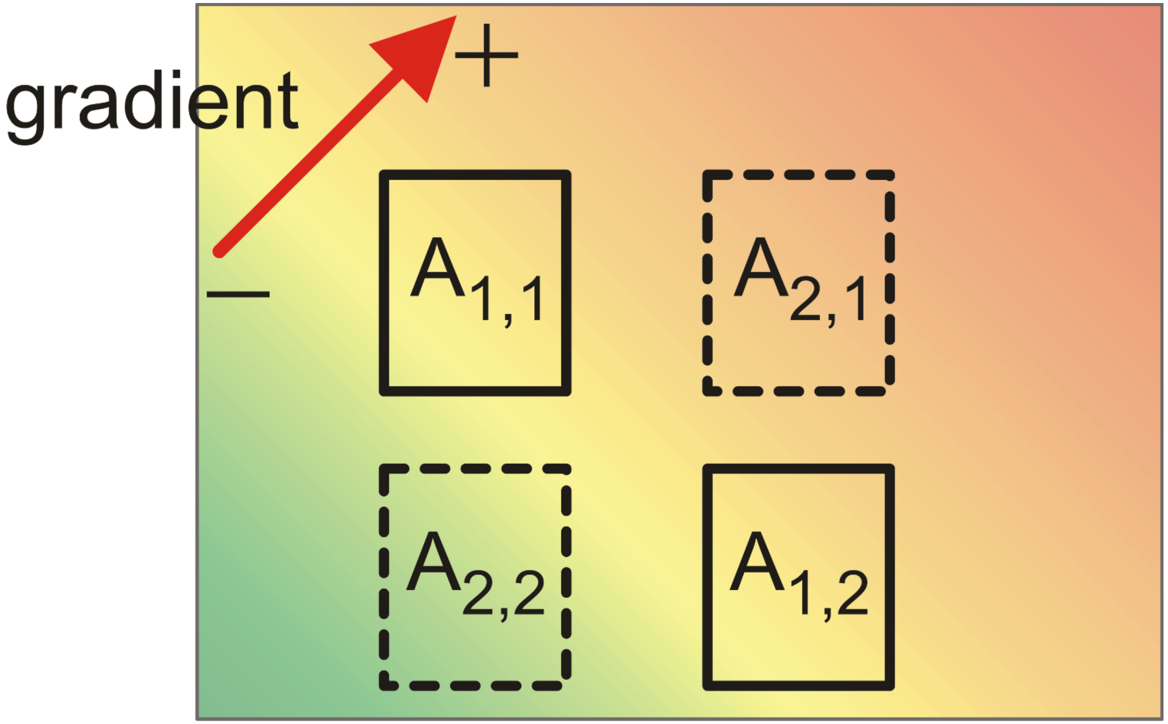
Unfortunately, in most cases, the direction of gradients is not predictable!

Layout rules that prevent device mismatch caused by gradients

- Rule 1 (obvious): Take the distance between objects as close as possible.
  (This rule is less effective for large devices)
- Rule 2: Use <u>common centroid</u> configurations.



Common centroid configuration: Oblique gradients

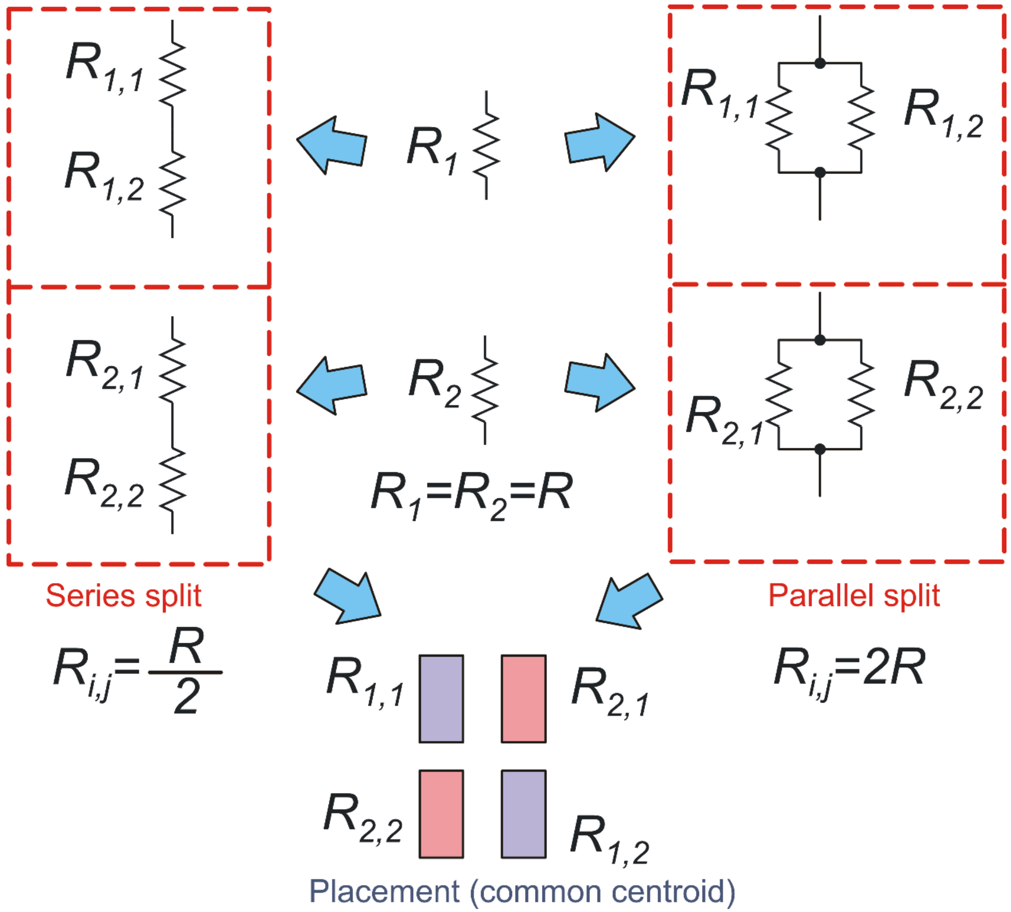


component	part	level
A_1	$A_{1,1}$	average
	$A_{1,2}$	average
A_2	$A_{2,1}$	high
	$A_{2,2}$	low

The common centroid configuration is effective also against oblique gradients..

Split and connect components in common centroid configurations

Case 1::Resistors

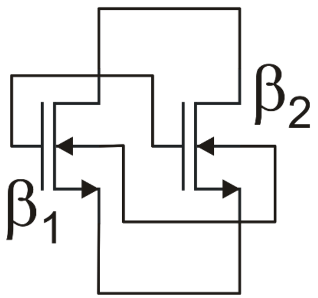


Series are preferred when resistors R_1 and R_2 are large

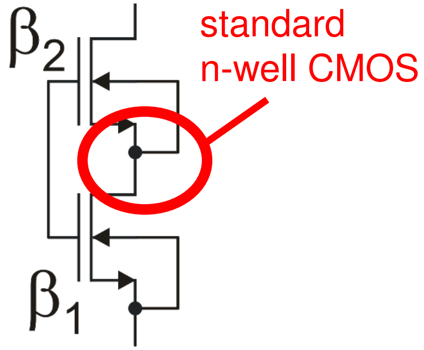
Parallels have to be preferred for small resistances

Split and connect components in common centroid configurations

Other devices -Properties of series and parallels

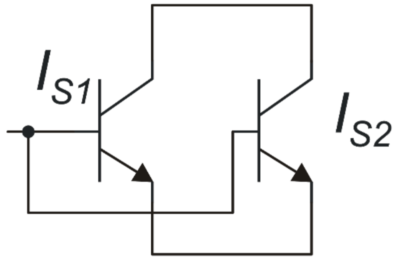


$$\beta_{eq}=\beta_1+\beta_2$$

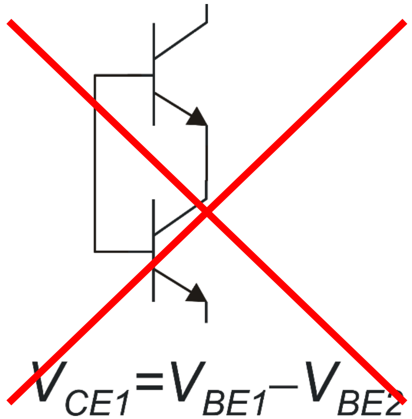


$$\frac{1}{\beta_{eq}} \cong \frac{1}{\beta_1}+\frac{1}{\beta_2}$$

Not accurate



$$I_{Seq}=I_{S1}+I_{S2}$$



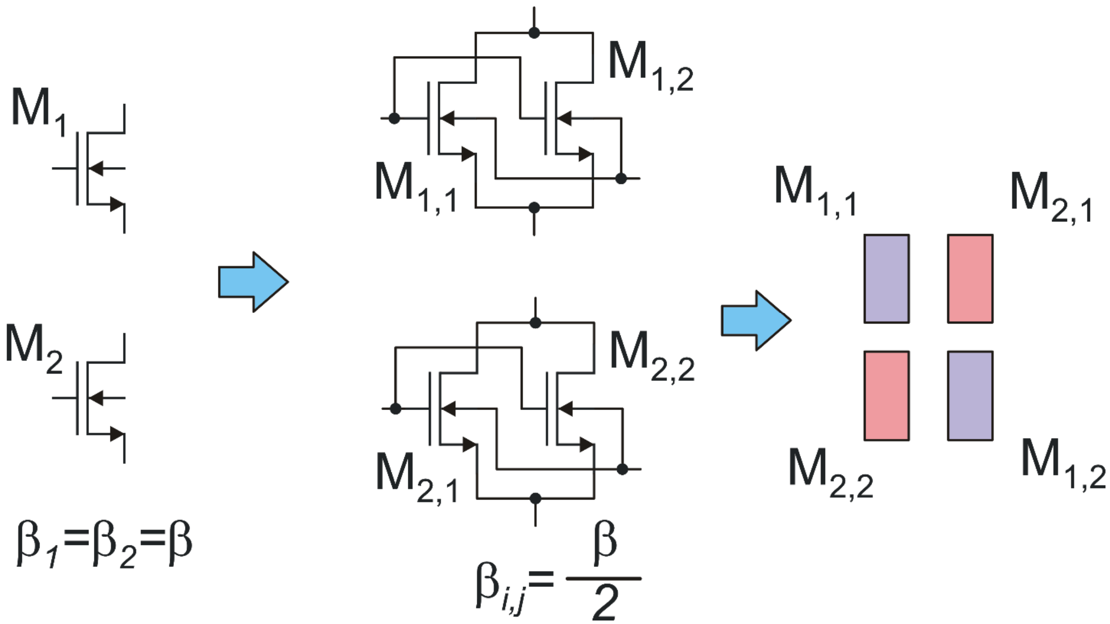
$$V_{CE1}=V_{BE1}-V_{BE2}\cong 0$$

Don't use!

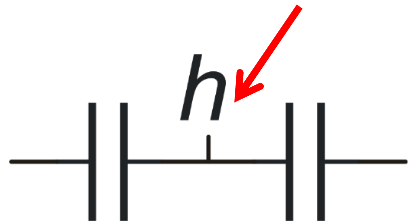
Accurate: Can be used in common centroid configurations

Split and connect components in common centroid configurations

Case 2: MOSFETS



Floating node (no dc path)



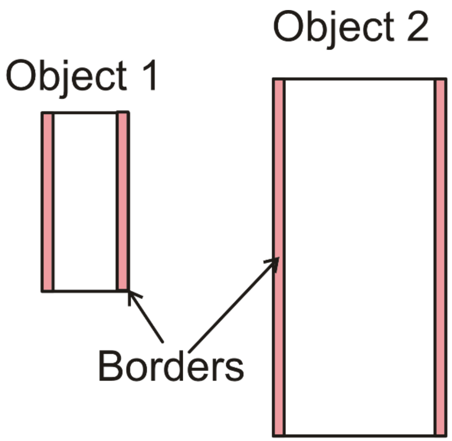
Series connections of capacitors have to be avoided as much as possible unless dc paths are provided for the floating node

BJTs: Same as Mosfets (parallels only)

Capacitors: Parallel connections are preferred (no floating nodes)

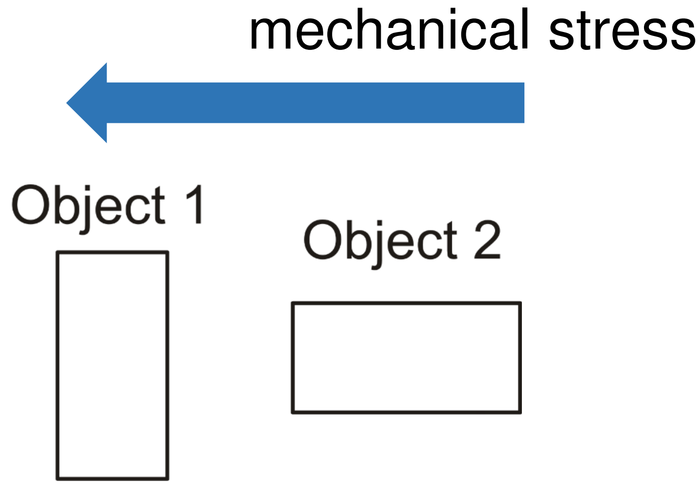
Other Layout rules for improving device matching

Wrong solutions



$$\frac{W_1}{L_1} = \frac{W_2}{L_2} \not\Rightarrow \begin{cases} R_1 = R_2 & \text{resistors} \\ \beta_1 = \beta_2 & \text{mosfets} \end{cases}$$

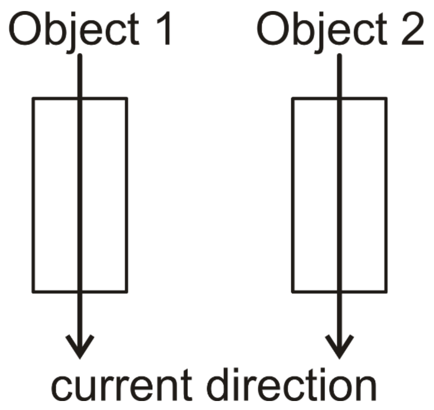
Different size: poor matching



Different orientation: poor matching

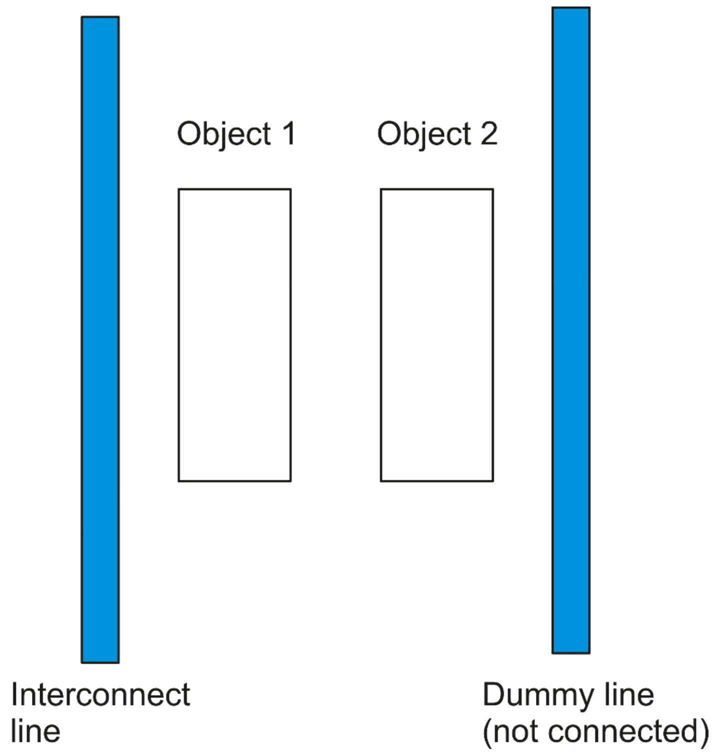
Other Layout rules for improving device matching

Same direction
(to match thermoelectric effects)



Temperature gradients develop extra voltage differences that depend on the current direction
(up to several hundred μVs

Same surroundings

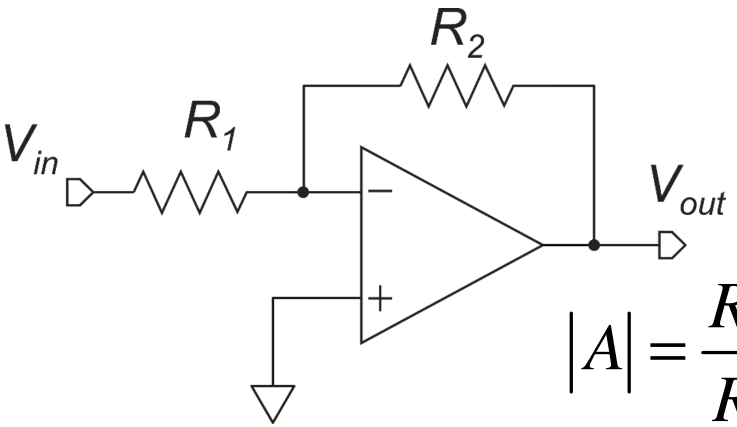


Summary of rules for a good device matching

- Devices must be nominally identical (same dimensions, same orientation)
- Device areas should be as large as possible (Pelgrom model)
- Place devices as close as possible
- Use common centroid configurations
- Same current direction for the two devices
- The devices should "see" the same surroundings

Rules to obtain accurate ratios

Example: accurate inverting amplifier with gain magnitude =**3**



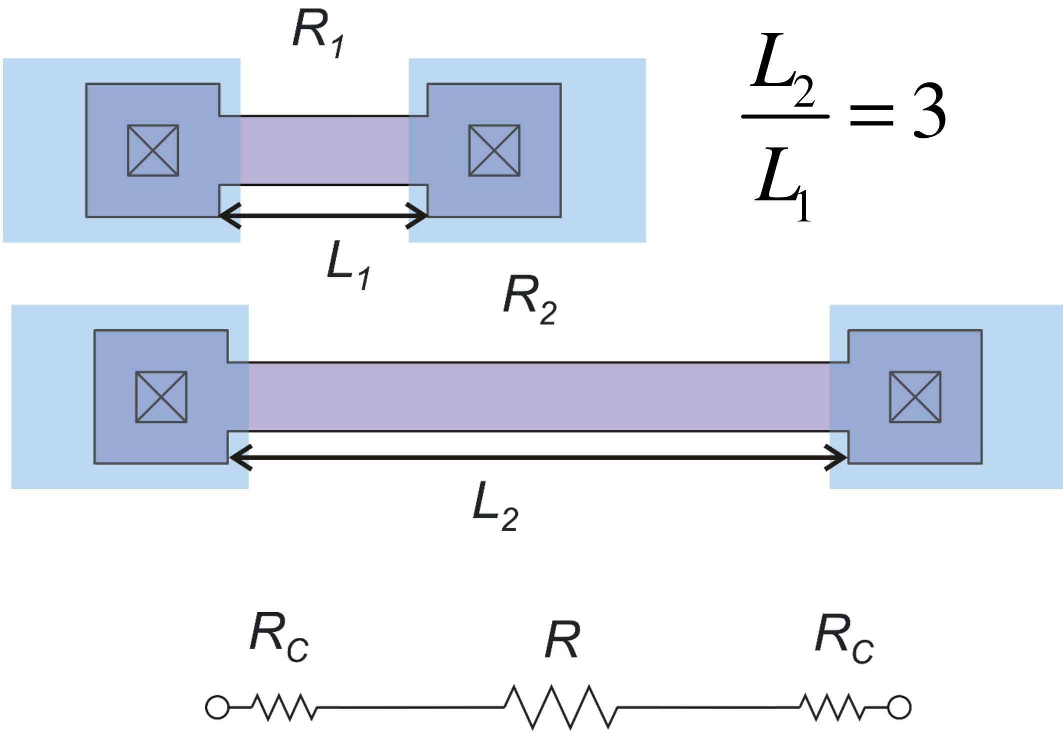
$$|A| = \frac{R_2}{R_1} = 3$$

$$|A| = \frac{3R + 2R_C}{R + 2R_C} = 3\frac{1+(2/3)x}{1+2x} < 3$$

$$x = \frac{R_C}{R}$$

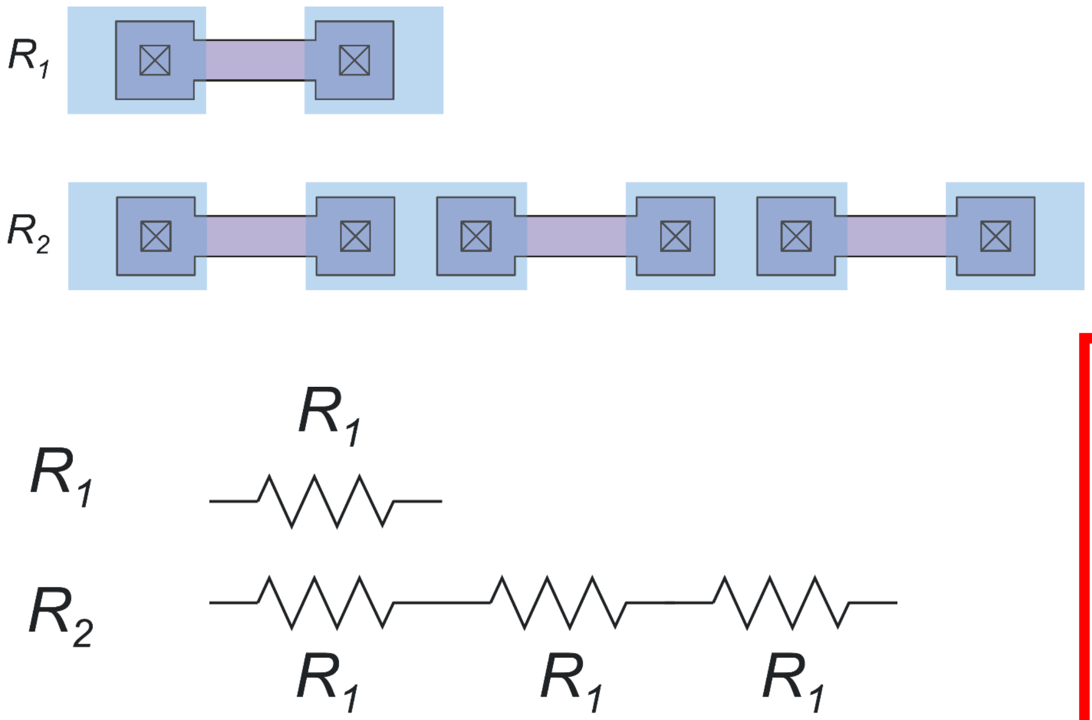
(e.g. with x=0.1, er=**11%**)

(systematic error)



$$\frac{L_2}{L_1} = 3$$

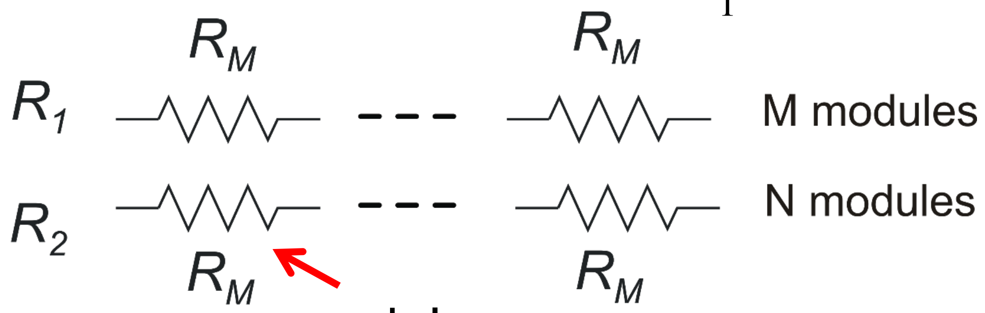
Accurate ratios: modular components



Both components R_1 and R_2 are obtained by adding different numbers of a single module.

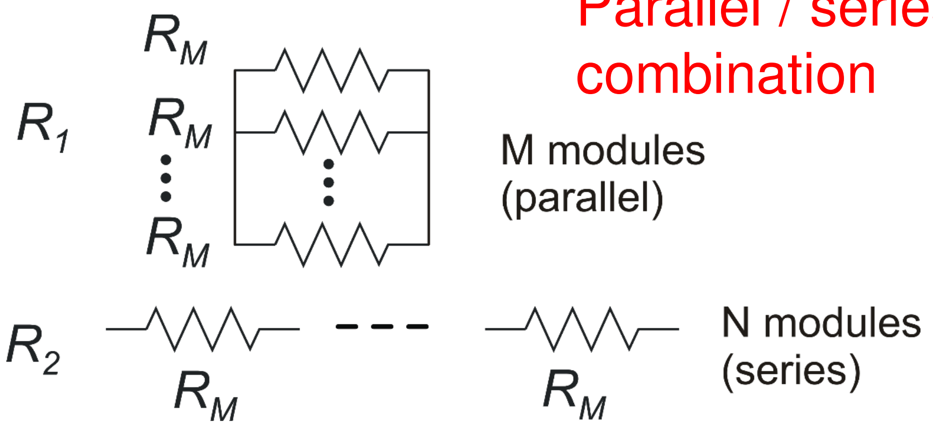
Generalization to Fractional ratios

$$\frac{R_2}{R_1} = \frac{N}{M}$$



Accurate ratios: modular components

Parallel / series combination

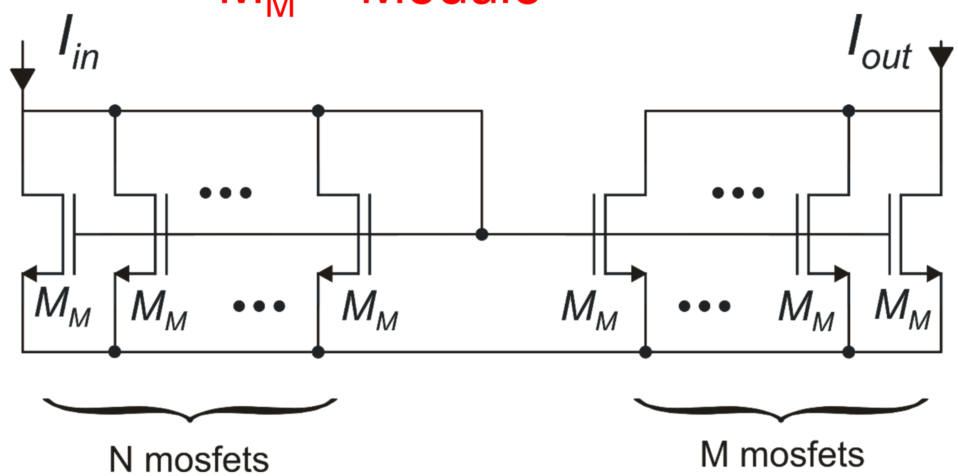


$$\frac{R_2}{R_1} = \frac{NR_M}{\frac{1}{M} R_M} = N \cdot M$$

Large ratios with less components

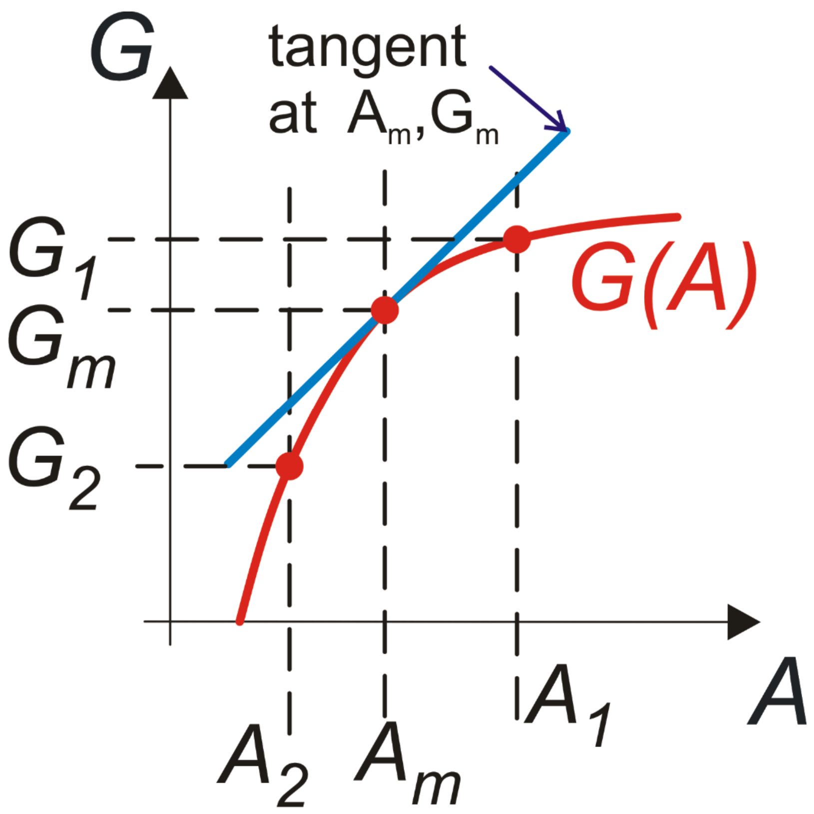
Current mirror with accurate gain

M_M = Module



$$\frac{I_{out}}{I_{in}} = \frac{\beta_2}{\beta_1} = \frac{M\beta_M}{N\beta_M} = \frac{M}{N}$$

Elements of error propagation theory



$$A_1 = A_m + \Delta A_1$$

$$A_2 = A_m + \Delta A_2$$

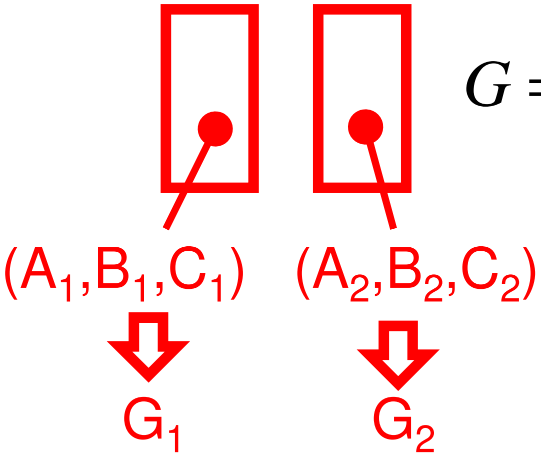
$$\Delta A = A_1 - A_2 = \Delta A_1 - \Delta A_2$$

$$G_1 = G(A_m + \Delta A_1) \cong G(A_m) + \Delta A_1 \left.\frac{dG}{dA}\right|_{A=A_m}$$

$$G_2 = G(A_m + \Delta A_2) \cong G(A_m) + \Delta A_2 \left.\frac{dG}{dA}\right|_{A=A_m}$$

$$G_1 - G_2 \cong (\Delta A_1 - \Delta A_2)\left.\frac{dG}{dA}\right|_{A=A_m} = \Delta A \left.\frac{dG}{dA}\right|_{A=A_m}$$

For multiple independent variables - general case



$$G = (A, B, C) \qquad \Delta G = G_1 - G_2 = G(A_1, B_1, C_1) - G(A_2, B_2, C_2)$$

$$P_m = (A_m, B_m, C_m) \quad \begin{cases} G_1 = G(A_m + \Delta A_1, B_m + \Delta B_1, C_m + \Delta C_1) \\ G_2 = G(A_m + \Delta A_2, B_m + \Delta B_2, C_m + \Delta C_2) \end{cases}$$

$$\begin{cases} G_1 = G(A_m, B_m, C_m) + \Delta A_1 \left.\dfrac{\partial G}{\partial A}\right|_{P_m} + \Delta B_1 \left.\dfrac{\partial G}{\partial B}\right|_{P_m} + \Delta C_1 \left.\dfrac{\partial G}{\partial C}\right|_{P_m} \\ G_2 = G(A_m, B_m, C_m) + \Delta A_2 \left.\dfrac{\partial G}{\partial A}\right|_{P_m} + \Delta B_2 \left.\dfrac{\partial G}{\partial B}\right|_{P_m} + \Delta C_2 \left.\dfrac{\partial G}{\partial C}\right|_{P_m} \end{cases}$$

$$\Delta G = G_1 - G_2 = \Delta A \left.\frac{\partial G}{\partial A}\right|_{P_m} + \Delta B \left.\frac{\partial G}{\partial B}\right|_{P_m} + \Delta C \left.\frac{\partial G}{\partial C}\right|_{P_m}$$

Error propagation: particular case 1

case 1:
posynomial expression

$$G(A,B,C)=A^{\alpha}B^{\beta}C^{\gamma}$$

α,β,γ : real exponents
A,B,C real positive variables

$$\left.\frac{\partial G}{\partial A}\right|_{P_m}=\alpha A_m^{\alpha-1}B_m^{\beta}C_m^{\gamma}$$

$$\left.\frac{\partial G}{\partial B}\right|_{P_m}=\beta A_m^{\alpha}B_m^{\beta-1}C_m^{\gamma}$$

$$\left.\frac{\partial G}{\partial C}\right|_{P_m}=\gamma A_m^{\alpha}B_m^{\beta}C_m^{\gamma-1}$$

Using: $\Delta G=\Delta A\left.\frac{\partial G}{\partial A}\right|_{P_m}+\Delta B\left.\frac{\partial G}{\partial B}\right|_{P_m}+\Delta C\left.\frac{\partial G}{\partial C}\right|_{P_m}$

$$\Delta G=\alpha A_m^{\alpha-1}B_m^{\beta}C_m^{\gamma}\Delta A+\beta A_m^{\alpha}B_m^{\beta-1}C_m^{\gamma}\Delta B+\gamma A_m^{\alpha}B_m^{\beta}C_m^{\gamma-1}\Delta C$$

Error propagation: particular case 1

case 1

$$G(A,B,C) = A^{\alpha} B^{\beta} C^{\gamma}$$

Relative variation (or relative error)

$$\frac{\Delta G}{G_m} = \frac{\Delta G}{G(P_m)} = \frac{\Delta G}{A_m^{\alpha} B_m^{\beta} C_m^{\gamma}}$$

$$\frac{\Delta G}{G_m} = \frac{\alpha A_m^{\alpha-1} B_m^{\beta} C_m^{\gamma} \Delta A + \beta A_m^{\alpha} B_m^{\beta-1} C_m^{\gamma} \Delta B + \gamma A_m^{\alpha} B_m^{\beta} C_m^{\gamma-1} \Delta C}{A_m^{\alpha} B_m^{\beta} C_m^{\gamma}}$$

$$\frac{\Delta G}{G_m} = \alpha \frac{\Delta A}{A_m} + \beta \frac{\Delta B}{B_m} + \gamma \frac{\Delta C}{C_m}$$

Sum of the single relative errors, weighted by the respective exponents

Error propagation: particular case 2

$$G(A,B,C)=\ln\left(A^{\alpha}B^{\beta}C^{\gamma}\right)$$

case 2: logarithm of a posinomial

$$Z=\left(A^{\alpha}B^{\beta}C^{\gamma}\right)$$

$$Z_m=\left(A_m^{\alpha}B_m^{\beta}C_m^{\gamma}\right)$$

$$\Delta G=\Delta Z\left.\frac{dG}{dZ}\right|_{Z=Z_m}=\Delta Z\left.\frac{d\left[\ln(Z)\right]}{dZ}\right|_{Z=Z_m}=\frac{\Delta Z}{Z_m}$$

$$\Delta G=\frac{\Delta Z}{Z}=\alpha\frac{\Delta A}{A_m}+\beta\frac{\Delta B}{B_m}+\gamma\frac{\Delta C}{C_m}$$

Here we have the absolute error of G, not the relative one.

Application to matching errors

- Generally, when dealing with matching errors: $A_m = \bar{A}$ (mean value)

- Matching errors has also the following basic property:

Linearity: G=A+B ΔG=ΔA+ΔB

G=kA, where k is a constant : ΔG=kΔA

- In the case of relative error, if G=kA: $\frac{\Delta G}{G} = \frac{\Delta A}{A}$

• Matching errors: statistical independence

- Matching errors of <u>different quantities</u> (e.g., quantities A,B,C) can be often considered independent from each other since they are mostly affected by microscopic irregularities, that do not show significant correlations when pairs of quantities are considered.
- In addition matching errors of <u>different device pairs</u> can be also considered independent, or, at least, uncorrelated.

$$G = k_1 A + k_2 B + k_3 C \Rightarrow \sigma_{\Delta G} = \sqrt{k_1^2 \sigma_{\Delta A}^2 + k_2^2 \sigma_{\Delta B}^2 + k_3^2 \sigma_{\Delta C}^2}$$